

10/539635

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Combined Form PTO/SB/08A&B INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			<i>Complete if Known</i>		
			Application Number	New Application	
			Confirmation Number		
			Filing Date	June 16, 2005	
			First Named Inventor	Yoshikazu TAKEDA et al.	
			Art Unit		
Examiner Name					
Sheet	1	of	2	Attorney Docket Number	052712

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
TSY	1	US 2001/0028755 A1		10-11-2001	Tomoyuki AKIYAMA

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
TSY	2	JP	2002-43696		02-08-2002	Fujitsu Ltd. (Cited in the Int'l. search Rpt)	Abstract
TSY	3	JP	9-326506		12-16-1997	Fujitsu Ltd. (Cited in the Int'l. search Rpt)	Abstract
TSY	4	JP	2001-255500		09-21-2001	Fujitsu Ltd. (Cited in the Int'l. search Rpt)	Abstract
TSY	5	JP	2000-196065		07-14-2000	Fujitsu Ltd. (Cited in the Int'l. search Rpt)	Abstract
TSY	6	JP	2000-340883		12-08-2000	Fujitsu Ltd. (Cited in the Specification)	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
	7	Y. NONOGAKI et al.; "Formation of InGaAs dots on InP substrate with lattice-matching growth condition by droplet heteroepitaxy", Inst. Phys. Conf. Ser. No. 162, Chapter 9, 1999, pp.469-473. (Cited in the Int'l. search report).	Yes
	8	Y. ARAKAWA et al.; "Multidimensional quantum well laser and temperature dependence of its threshold current", Appl. Phys. Lett. Vol.40, No. 11, June 1, 1982, pp.939-941. (Cited in the Specification).	Yes
	9	M. ASADA et al.; "Gain and the Threshold of Three-Dimensional Quantum-Box Lasers", IEEE Journal of Quantum Electronics, Vol. QE-22, No. 9, Sept.1986, pp.1914-1921. (Cited in the Specification)	Yes
	10	K. J. VAHALA, "Quantum Box Fabrication Tolerance and Size Limits in Semiconductors and Their Effect on Optical Gain", IEEE, J. Quantum Electronics, Vol.24, No. 3, March 1988, pp.522-531. (Cited in the Specification)	Yes
	11	H. SAKAKI; "Quantum Wire Superlattices and Coupled Quantum Box Arrays: A Novel Method to Suppress Optical Phonon Scattering in Semiconductors", Jpn. J. Appl. Phys, Vol. 28, 1989, pp.L314-L316. (Cited in the Specification).	Yes
	12	N. KIRSTAEDTER et al.; "Low threshold, large T ₀ injection laser emission from (InGa) As quantum dots", Electronics letters, Vol. 30, No. 17, Aug. 18, 1994, pp.1416-1417. (Cited in the Specification).	
TSY	13	Y. NONOGAKI et al.; "InAs dots grown on InP (001) by droplet hetero-epitaxi using OMVPE", Mat. Sci. & Eng., Vol. B51, 1998, pp.118-121. (Cited in the Specification).	Yes

Examiner Signature	/Thanhha Pham/	Date Considered	07/22/2007
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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NON PATENT LITERATURE DOCUMENTS			
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TSP	14	R. OGA et al.; "Room temperature electroluminescence at 1.55 μ m from InAs quantum dots grown on (001) InP by droplet hetero-epitaxy); 10 th Int. Sump. Nanostructures: Physics and Technolgy, St. Petersburg, Russia, June 17-21, 2000.	Yes
	15	Woo-Sik LEE et al.; "Fabrication and Application of InAs quantum dots by droplet-hetero epitaxy on GaInAsP and AlInAs lattice-matched with InP substrate" The Institute of Electronics, Vol. 103, No. 47.	Abstract

Examiner Signature		Date Considered	
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